

**GROWTH AND CHARACTERIZATION OF ZnCr₂Se₄ – SINGLE CRYSTALS
DOPED WITH NEODYMIUM**

Barsova Z., Jendrzejewska I., Groń T., Kusz J., Pietrasik E.,
Goryczka T., Sawicki B., Duda H.
University of Silesia, Katowice, Poland
z.v.barsova@gmail.com

Transition metals chalcogenides with general formula AB₂X₄ (A and B are transition metals, X is a chalcogen element: O, S, Se, Te) are a very wide group of chemical compounds, having (possessing) a large spectrum of physical properties that make them very attractive to potential application [1]. The Cr-based selenospinel (ACr₂Se₄, A = Cd, Zn, Cu, Hg) possess interesting properties due to coexistence of frustration and strong coupling among spin, charge, orbital and lattice degrees of freedom. The ZnCr₂Se₄ matrix, belonging to family of spinel compounds, is a *p*-type semiconductor and antiferromagnet with normal spinel structure. The new ZnCr₂Se₄-single crystals doped with neodymium (0.05, 0.08 and 0.10) were obtained using chemical vapour transport method with anhydrous CrCl₃ as a transport agent, ZnSe and NdSe as a substrates. In order to determine the reaction conditions, the thermodynamic calculations were done. Analysis of the obtained ZnCr₂Se₄:Nd single crystals by X-ray diffraction, SEM and DSC/TG showed that these crystals are chemically pure, crystalline, occur in a cubic structure (SG: *Fd3m*) and thermally stable. The electrical and magnetic studies of neodymium doped ZnCr₂Se₄ – single crystals showed a semiconducting behavior, an antiferromagnetic (AFM) order and a short-range ferromagnetic (FM) interactions. Our results are generally in good agreement with our expectation. Neodymium ions had a stabilizing effect on both long-range AFM and short-range FM interactions, without spin frustration. However, the presence of neodymium ions having a large ion radius resulted in an increase in the Cr-Se bond lengths, leading to a significant reduction in short-range FM interactions compared to those of the bond lengths for the ZnCr₂Se₄ matrix. These crystals can have potentially application in magneto-electronic or magneto-optical switching devices.

References

1. L. Q. Yan, J. Shen, Y. X. Li, F. W. Wang, Z. W. Jiang, F. X. Hu, J. R. Sun, B. G. Shen, Appl. Phys. Lett. 90 (2007) 262502.